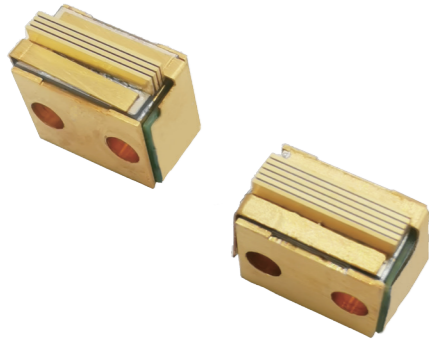


# GS1 Series Diode laser Vertical stacks



## Key Features

- ◆ Sealed package, compact design
- ◆ AuSn sintering
- ◆ Available to work under high-temperature
- ◆ High power density
- ◆ High reliability

## Technical Specifications

(Test temperature: 25°C Pulse width: 250μs Repetition rate: 50Hz)

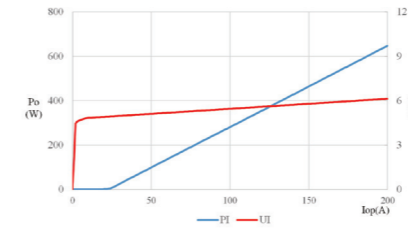
	Parameters	Unit	R808±3-600-GS1-3X1	R808±3-1000-GS1-5X1
Optical	Center Wavelength	nm	808±3	808±3
	Spectral Width (FWHM)	nm	≤5	≤5
	Duty Ratio	%	≤2	≤2
	Peak Power	W	600	1000
	Quantity of Bars	-	3	5
	Width of Bars	mm	10	10
	Spaces between Bars	mm	0.4	0.4
	Fast axis divergence angle (FWHM)	°	35	35
	Slow axis divergence angle (FWHM)	°	10	10
	Polarization	-	TE	TE
Electrical	Operating Current	A	200	200
	Threshold Current	A	25	25
	Operating Voltage	V	6	10
	Conversion Efficiency	%	50	50
Environment	Operating Temperature	°C	-20 ~ 70	-20 ~ 70
	Storage Temperature	°C	-40 ~ 80	-40 ~ 80

Notes:

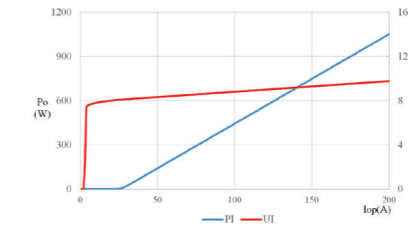
1. Accept to customize the wavelength of 940nm;
2. Available to pack 1-5 bars;
3. Spaces between bars are available to be customized.

## Applications

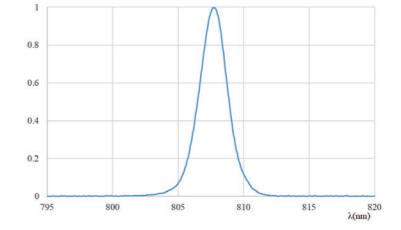
- Pumping source
- Material processing
- Laser lighting
- Medical cosmetology
- Scientific research applications



PIV Graph  
R808±3-600-GS1-3X1

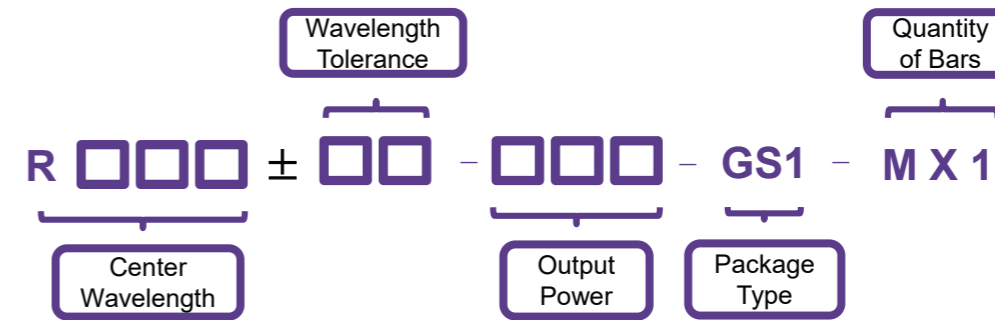


PIV Graph  
R808±3-1000-GS1-5X1



Spectrum

## Part Numbering Schema



## Mechanical Drawings (in mm)

